



LED1550-03

- Infrared light emitting diode
- 1550 nm, 2.5 mW
- High radiant intensity
- InGaAsP



Description

LED1550-03 is a InGaAsP based Light Emitting Diode emitting at 1550 nm with rated output power of 2.5 mW, mounted on a lead frame with a 5 mm clear epoxy resin

Maximum Ratings

Parameter	Symbol	Values		Unit
		Min.	Max.	
Power Dissipation ($T_A=25^\circ\text{C}$)	P_D		120	mW
Forward Current ($T_A=25^\circ\text{C}$)	I_F		100	mA
Pulse Forward Current ($T_A=25^\circ\text{C}$)*	I_{FP}		1000	mA
Reverse Voltage ($T_A=25^\circ\text{C}$, $I_R=10\mu$)	V_R		5	V
Operating Temperature	T_{CASE}	- 30	+ 85	$^\circ\text{C}$
Storage Temperature	T_{STG}	- 40	+ 100	$^\circ\text{C}$
Soldering Temperature*	T_{SOLDER}		265	$^\circ\text{C}$

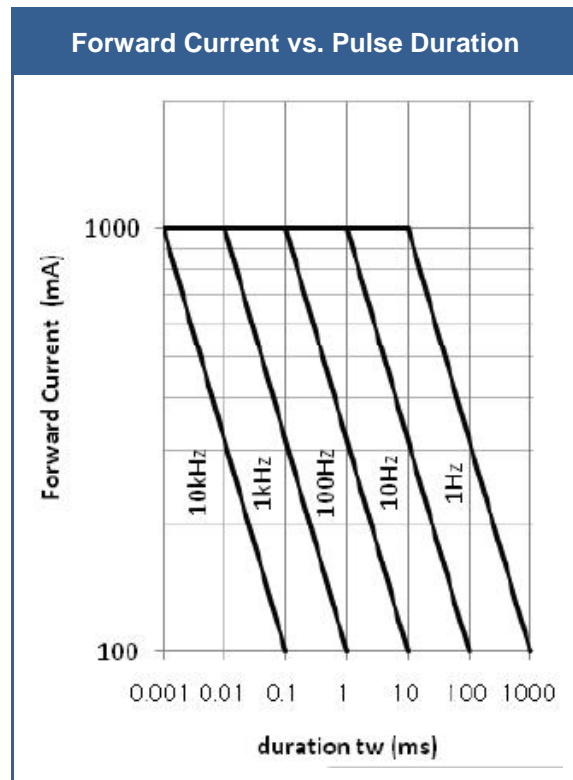
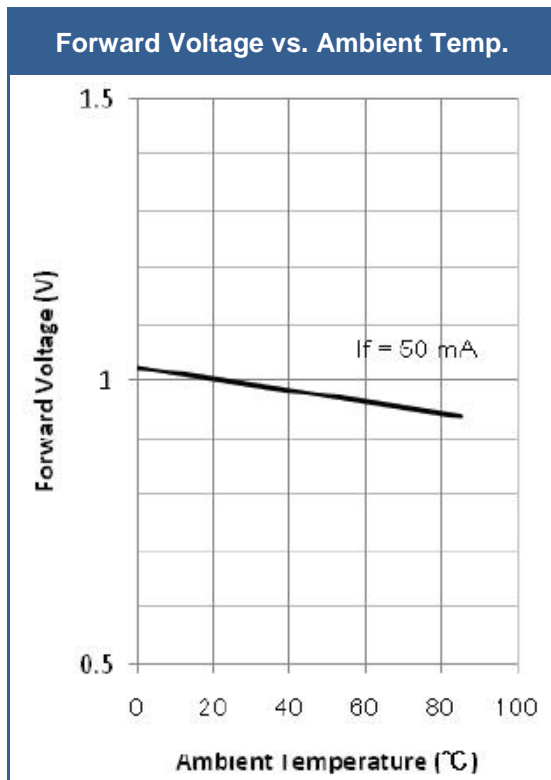
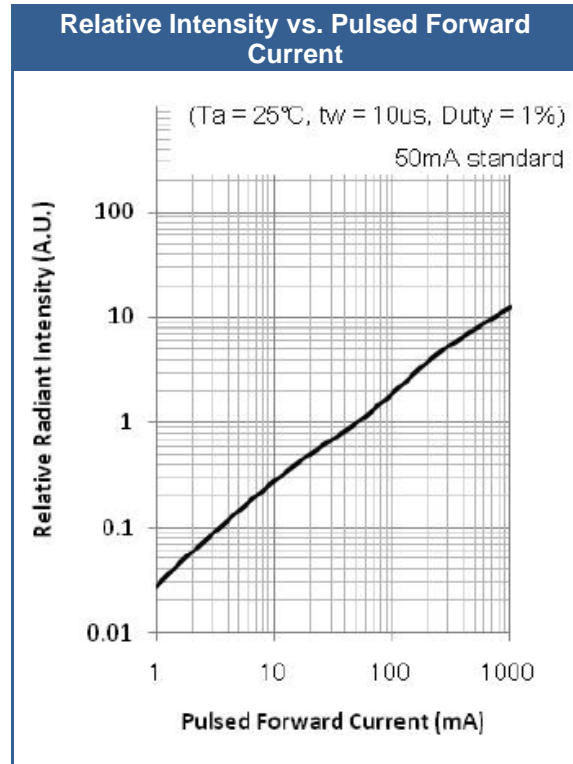
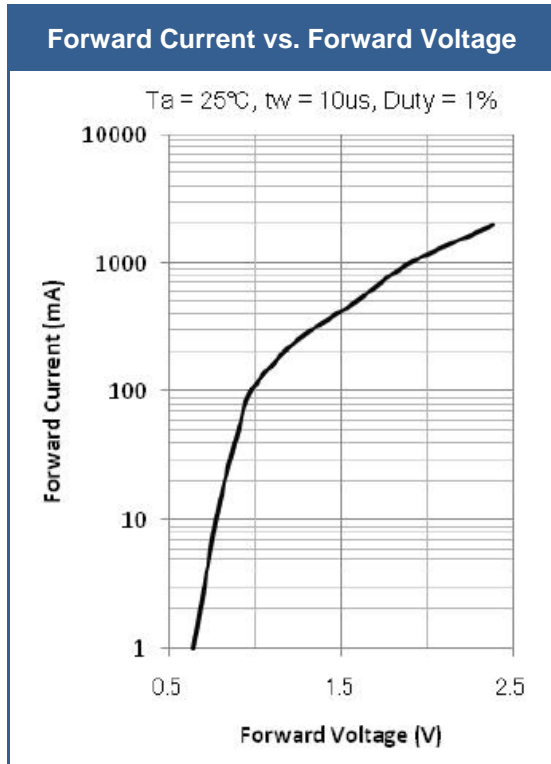
* must be completed within 3 seconds at 265 $^\circ\text{C}$

Electro-Optical Characteristics ($T_{CASE} = 25^\circ\text{C}$, $I_F = 50\text{ mA}$)

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Peak Wavelength	λ_P	1500	1550	1600	nm
Spectral Width (FWHM)	$\Delta\lambda$		100		nm
Radiated Power	P_O	1.3	2.5		mW
Radiated Intensity	I_E		18		mW/sr
Forward Voltage	V_F		0.9	1.5	V
Forward Current	I_F		50		mA
Reverse Current	I_R			10	μA
Viewing Half Angle	$\Theta_{1/2}$		± 15		deg.
Rise/Fall time	t_R, t_F		10/10		ns

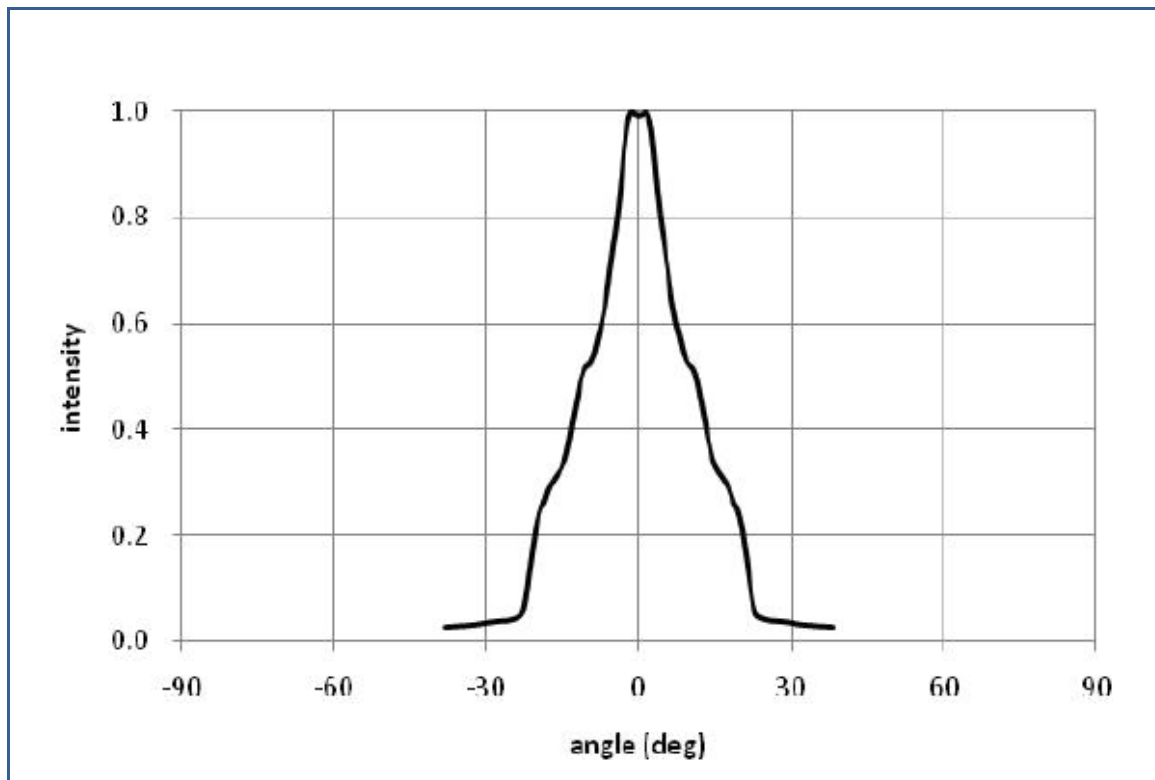
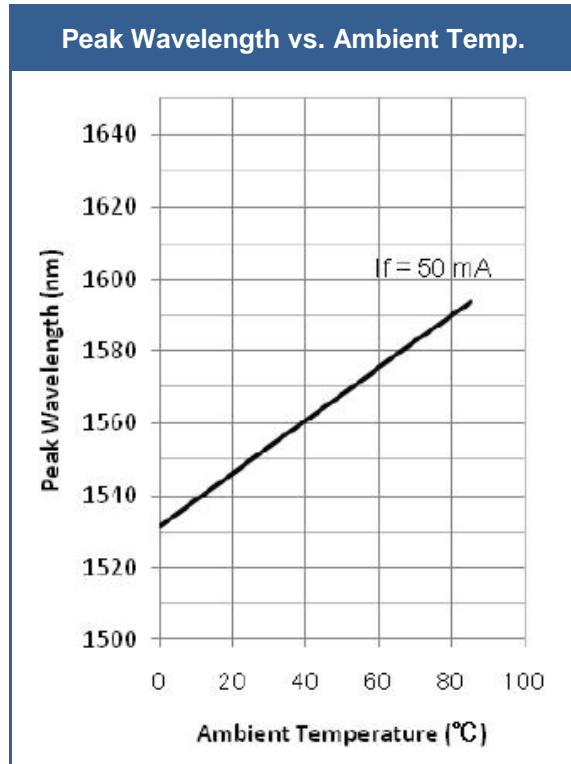
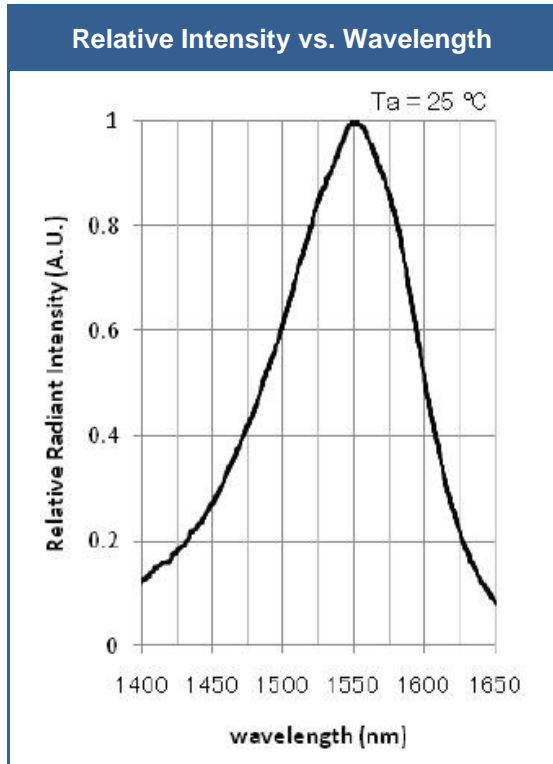


Performance Characteristics



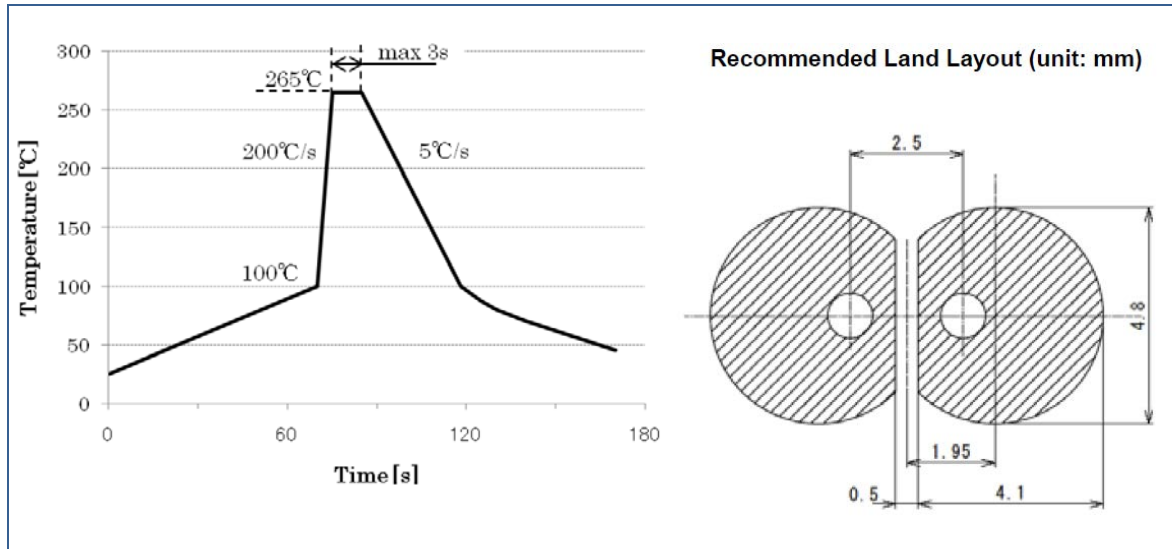


Performance Characteristics



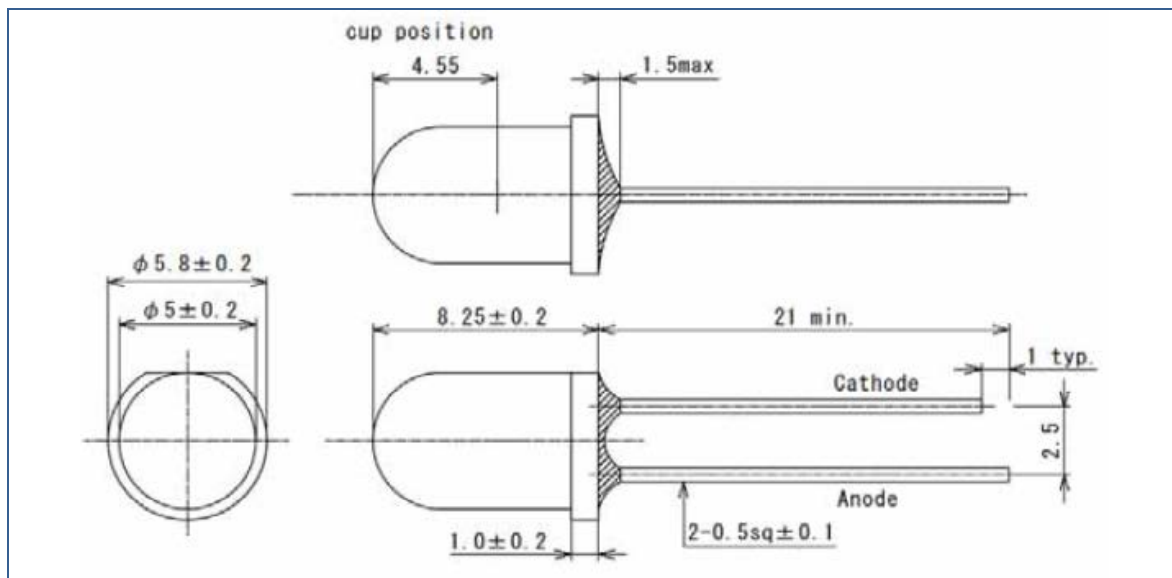


Soldering



- Soldering must be completed within 3 seconds at a maximum temperature of 265°C

Drawing



All dimensions in mm